

Features

- TrenchFET® Power MOSFET: 1.8-V Rated
- Gate-Source ESD Protected: 2000 V
- High-Side Switching
- Low On-Resistance: 1.2 Ω
- Low Threshold: 0.8 V (typ)
- Fast Switching Speed: 14 ns
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation

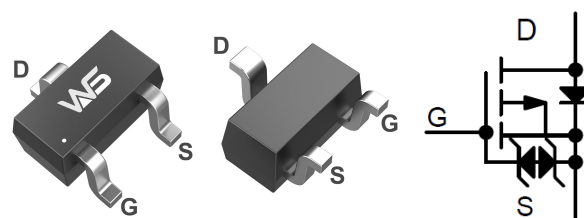
Product Summary

BVDSS	RDSON	ID
-20V	1200m Ω	-0.35A

Applications

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

SOT-523 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 6	V
$I_D@T_c=25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -4.5V ¹	-0.35	A
$I_D@T_c=70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -4.5V ¹	-0.4	A
I_{DM}	Pulsed Drain Current ²	-1	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	0.15	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	125	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	80	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

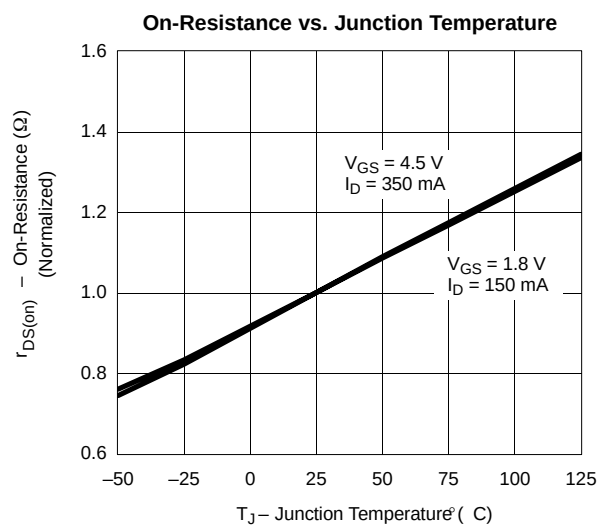
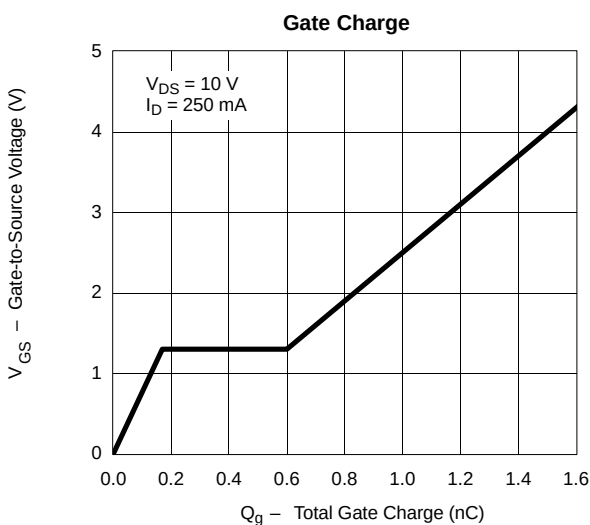
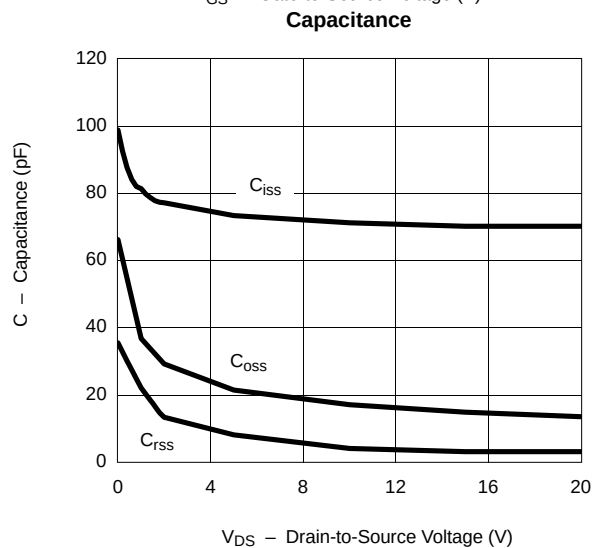
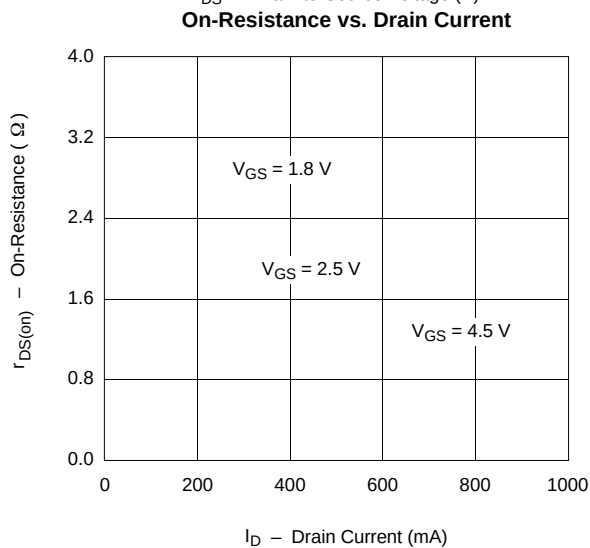
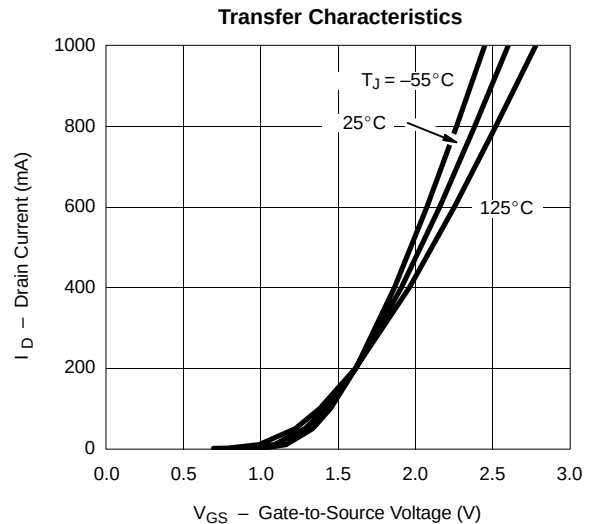
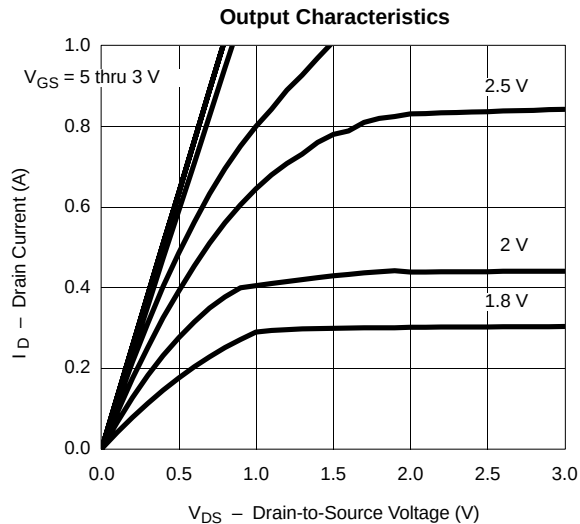
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.016	---	V/ $^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-4.5V$, $I_D=-0.250A$	---	0.8	1.2	Ω
		$V_{GS}=-2.5V$, $I_D=-0.250A$	---	1.2	1.6	
		$V_{GS}=-1.8V$, $I_D=-0.01A$	---	1.8	2.7	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-0.45	---	---	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	3.97	---	mV/ $^{\circ}\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-16V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	-1	μA
		$V_{DS}=-16V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 8V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V$, $I_D=-1A$	---	6.2	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	9.5	12	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15V$, $V_{GS}=-4.5V$, $I_D=-1A$	---	3.0	---	nC
Q_{gs}	Gate-Source Charge		---	1	---	
Q_{gd}	Gate-Drain Charge		---	0.8	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V$, $V_{GS}=-4.5V$, $R_G=3.3\Omega$, $I_D=-1A$	---	5	---	ns
T_r	Rise Time		---	9	---	
$T_{d(off)}$	Turn-Off Delay Time		---	35	---	
T_f	Fall Time		---	11	---	

Notes

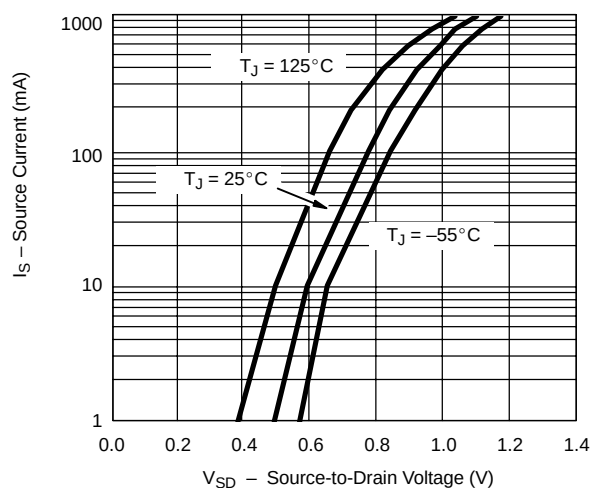
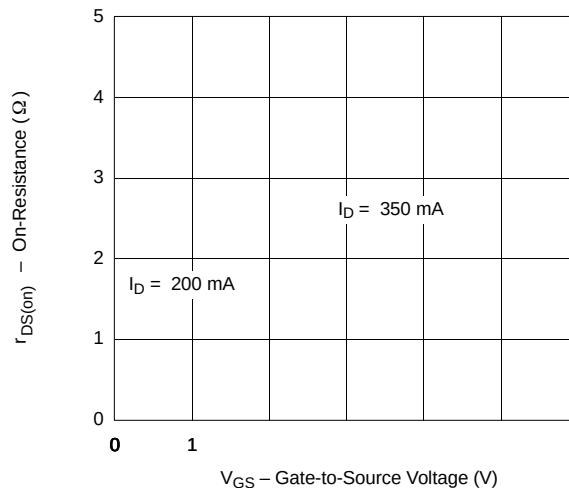
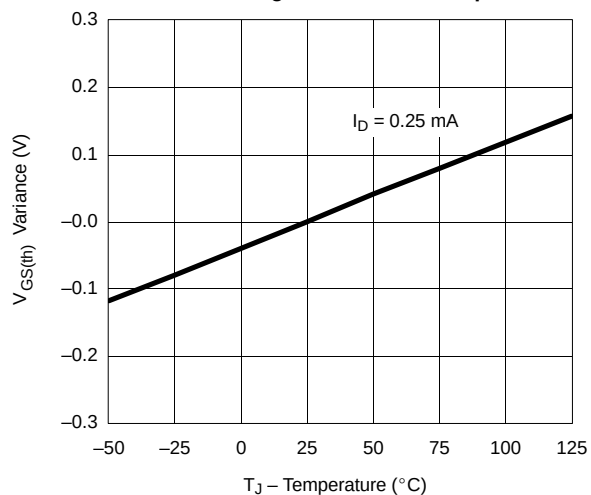
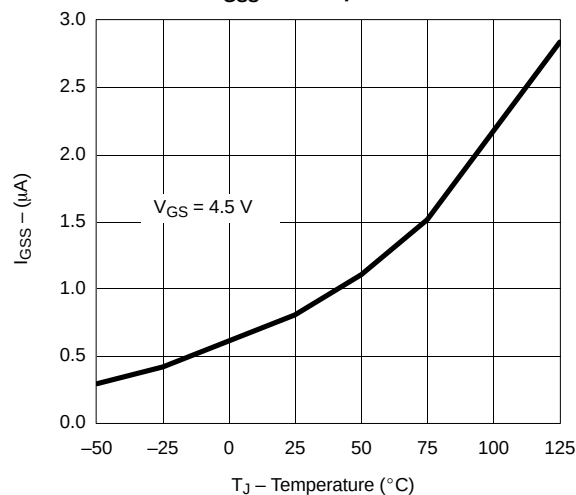
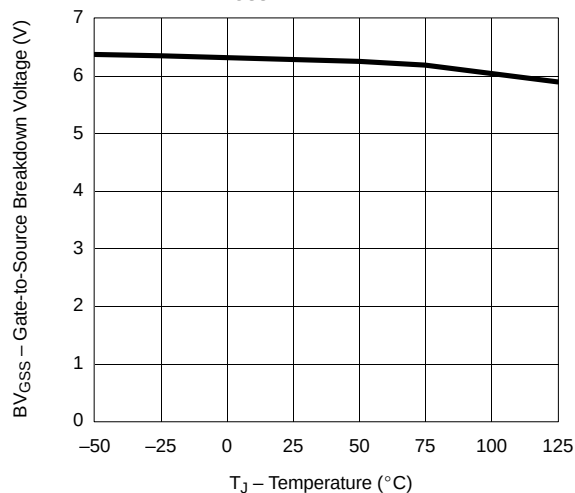
- Pulse test; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

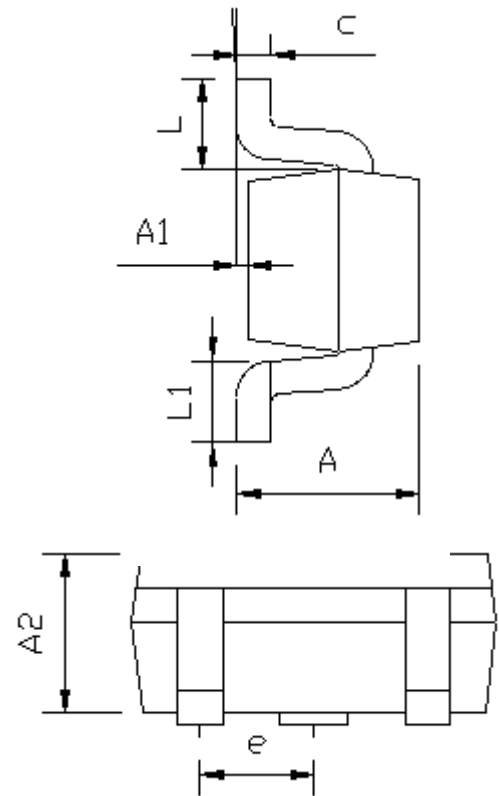
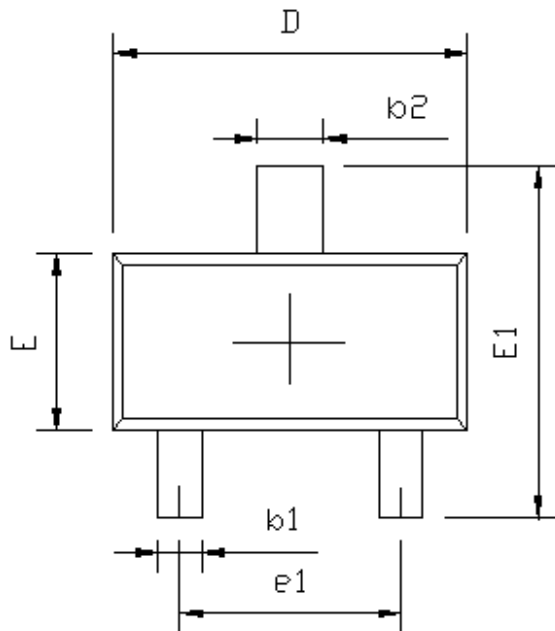
Typical Characteristics

For the following graphs, p-channel negative polarities for all voltage and current values are represented as positive values.

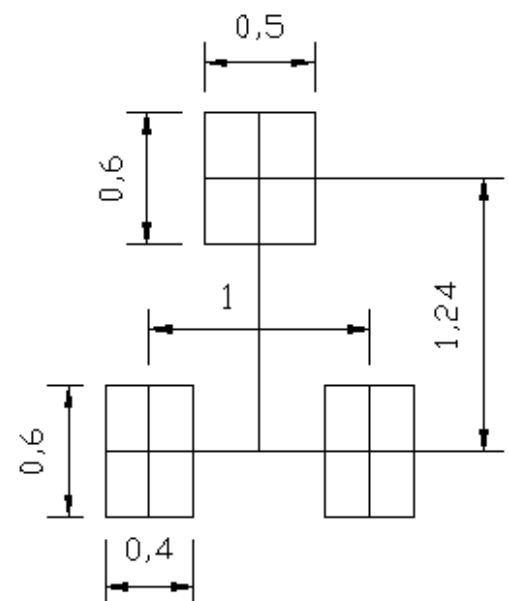


Typical Characteristics

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage Variance vs. Temperature

IGSS vs. Temperature

BVGS vs. Temperature


SOT-523


SYMBOLS	SOT-523			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN


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